Case Docket No. SEPP15.001AUS

Date: January 10, 2002



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s)

SKARP et al.

Appl. No.

10/003,749

Filed

October 23, 2001

For

PROCESS FOR

PRODUCING ALUMINUM OXIDE FILMS AT LOW TEMPERATURES

Examiner

Unknown

Group Art Unit:

Unknown

ETTER RECEIVED

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TC 1700

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents,

January 10, 2002

Adeel S. Akhtar, Reg. No. 41,349

(Date)

Washington, D.C. 20231, on

TRANSMITTAL LETTER

COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

Dear Sir:

Enclosed for filing in the above-identified application are:

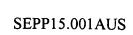
- (X) An Information Disclosure Statement.
- (X) A Form PTO-1449 with thirteen (13) references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.

Adeel S. Akhtar

Registration No. 41,349

Attorney of Record

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## IN THE UNIFIED STATES PATENT AND TRADEMARK OFFICE

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Filed	:	October 23, 2001	) )
App. No.	:	10/003,749	)
Applicant	:	SKARP et al.	) Group Art Unit: Unknown

Dear Sir:

Enclosed is form PTO-1449 listing thirteen (13) references that are also enclosed. This Information Disclosure Statement is being filed within three months of the filing date of this application or upon filing if this is a CPA or RCE, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: January 10, 2001

By: Adeel S. Akhtar

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U.S. DEPARTMENT OF COMMERCE FORM PTQ-1449 ATTY. DOCKET NO. APPLICATION NO. PATENT AND TRADEMARK OFFICE SEPP15.001AUS 10/003,749 INFORMATION DISCLOSURE STATEMENT FEB 2 6 2002 BY APPLICANT **APPLICANT** SKARP et al. (USE SEVERAL SHEETS IF NECESSARY) FILING DATE **GROUP** 1767 -Unknown-October 23, 2001

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EXAMINER INITIAL/		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS		DATE OPRIATE)
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XII	3	JP58033841	28.02.83	Japan	N.S.	30.		
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YIV	5	Kattelus, H. et al., "Electrical Properties of Tantalum Based Composite Oxide Films," Mat. Res. Soc. Symp. Proc., Vol. 284, pp. 511-516 (1993).						
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EXAMINER		DATE CONSIDERED	5/31/93
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\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.